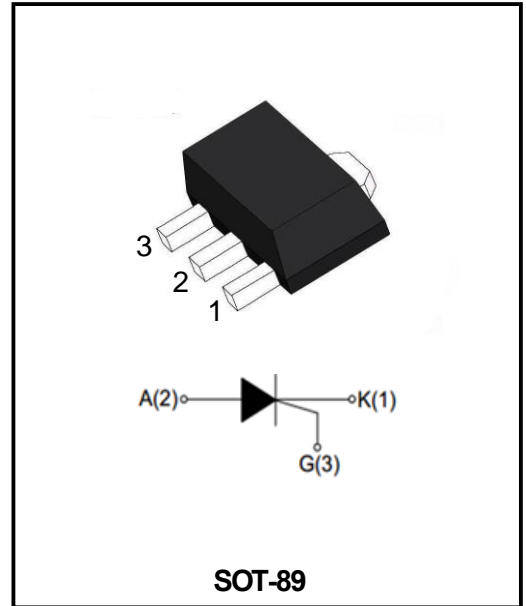


0.8A Sensitive Gate SCRs

Product Summary

| Symbol | Value | Unit |
|---------------------|---------|------|
| $I_{T(RMS)}$ | 0.8 | A |
| V_{DRM} V_{RRM} | 600/800 | V |
| V_{TM} | 1.55 | V |



Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

Application

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.

Absolute maximum ratings (Ta=25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|--------------|------------------|------------------|
| Repetitive peak off-state voltage | V_{DRM} | 600/800 | V |
| Repetitive peak reverse voltage | V_{RRM} | 600/800 | V |
| RMS on-state current | $I_{T(RMS)}$ | 0.8 | A |
| Non repetitive surge peak on-state current (full cycle, F=50Hz) | I_{TSM} | 8 | A |
| I^2t value for fusing (tp=10ms) | I^2t | 0.32 | A ² S |
| Critical rate of rise of on-state current ($I_G = 2 \times I_{GT}$) | di_T/dt | I - II -III 50 | A/ μ s |
| Peak gate current tp=20 μ s, Tj=110°C | I_{GM} | 0.2 | A |
| Average gate power dissipation Tj=110°C | $P_{G(AV)}$ | 0.1 | W |
| Junction Temperature | T_J | -40~+110 | °C |
| Storage Temperature | T_{STG} | -40 ~+150 | °C |

Electrical characteristics (TA=25°C, unless otherwise noted)

| Parameter | Symbol | Test Condition | Value | | | Unit |
|--|-----------|--|-------|-----|-----|------------|
| | | | Min | Typ | Max | |
| Gate trigger current | I_{GT} | $V_D=12V, I_T=10mA, T_j=25^\circ C, Fig. 6$ | 10 | - | 200 | μA |
| Gate trigger voltage | V_{GT} | $V_D=12V, I_T=10mA, T_j=25^\circ C$ | - | - | 0.8 | V |
| Non-triggering gate voltage | V_{GD} | $V_D=1/2V_{DRM}, R_{GK}=1k\Omega, T_j=110^\circ C$ | 0.2 | - | - | V |
| Holding current | I_H | $V_D=12V, I_G=0.5mA,$ | - | - | 3 | mA |
| Latching current | I_L | $R_{GK}=1k\Omega, T_j=25^\circ C, Fig. 6$ | - | - | 4 | mA |
| Critical-rate of rise of commutation voltage | dV_D/dt | $V_D=67\%V_{DRM}, T_j=110^\circ C$ | 10 | - | - | V/ μs |

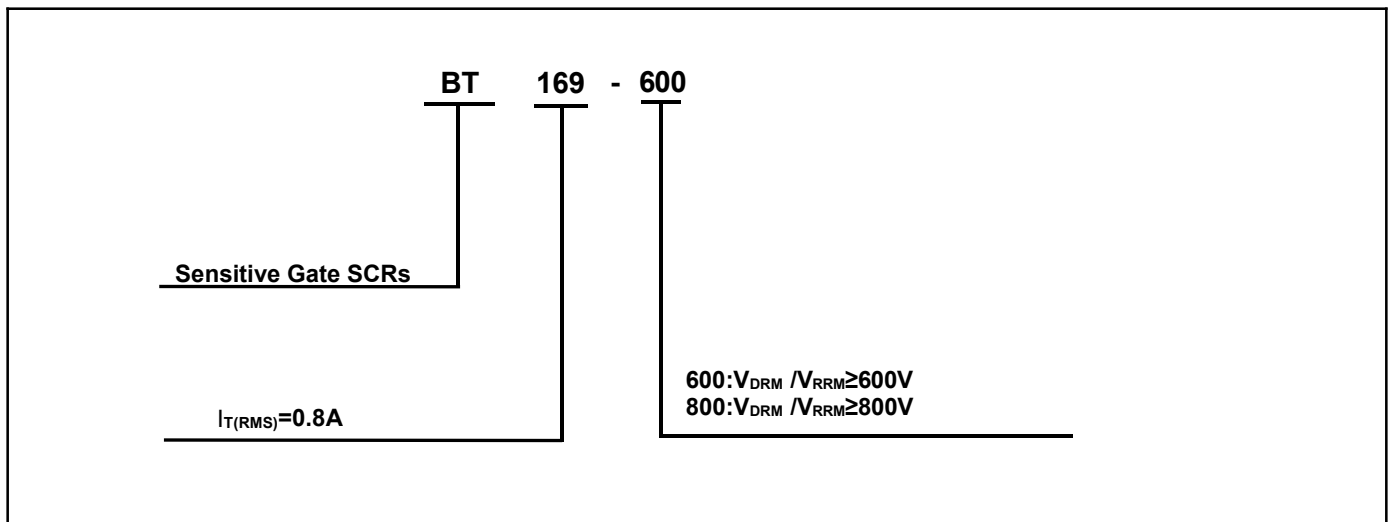
STATIC CHARACTERISTICS

| | | | | | | | |
|-----------------------------------|-----------|--|-------------------|---|-----|-----|---------|
| On-state Voltage | V_{TM} | $I_T=1.2A, t_p=380\mu s, T_j=25^\circ C, Fig. 4$ | - | - | 1.5 | V | |
| Repetitive Peak Off-State Current | I_{DRM} | $V_D=V_{DRM}=V_{RRM}$ | $T_j=25^\circ C$ | - | - | 5 | μA |
| Repetitive Peak Reverse Current | I_{RRM} | | $T_j=110^\circ C$ | - | - | 100 | μA |

THERMAL RESISTANCES

| | | | | | |
|--------------------|---------------|---------------------|------|-----|--------------|
| Thermal resistance | $R_{th(j-c)}$ | Junction to case | TYP. | 32 | $^\circ C/W$ |
| | $R_{th(j-a)}$ | Junction to ambient | TYP. | 100 | $^\circ C/W$ |

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

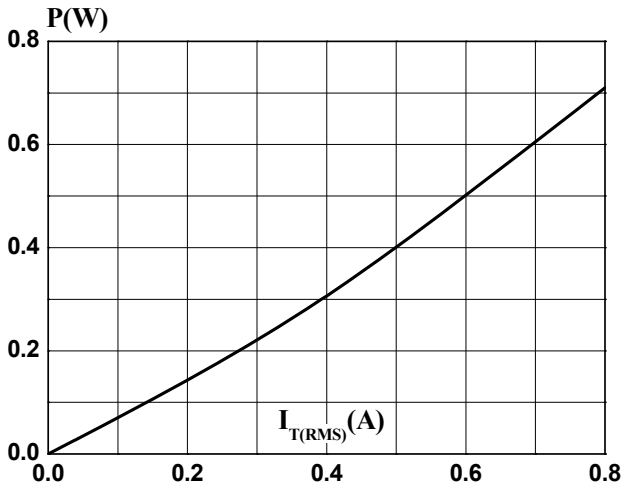


FIG.2: RMS on-state current versus case temperature (full cycle)

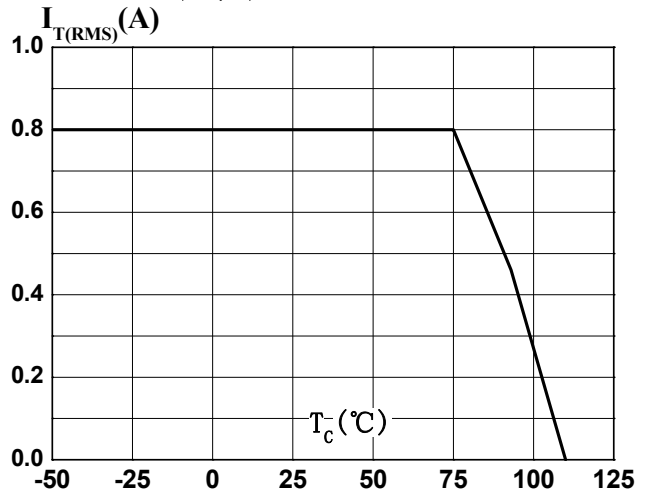


FIG.3: Surge peak on-state current versus number of cycles

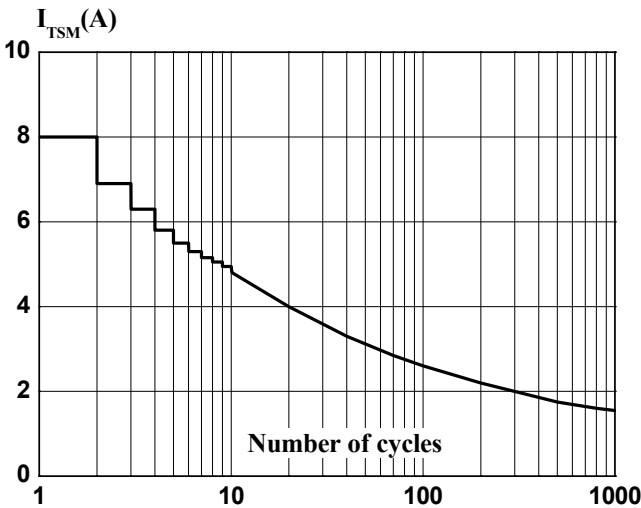


FIG.4: On-state characteristics (maximum values)

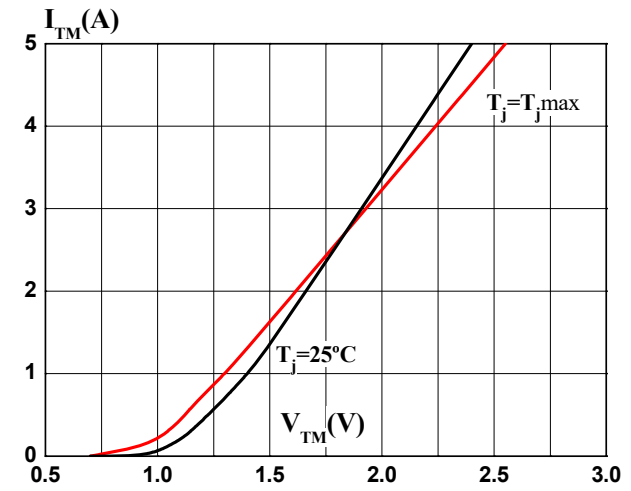


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

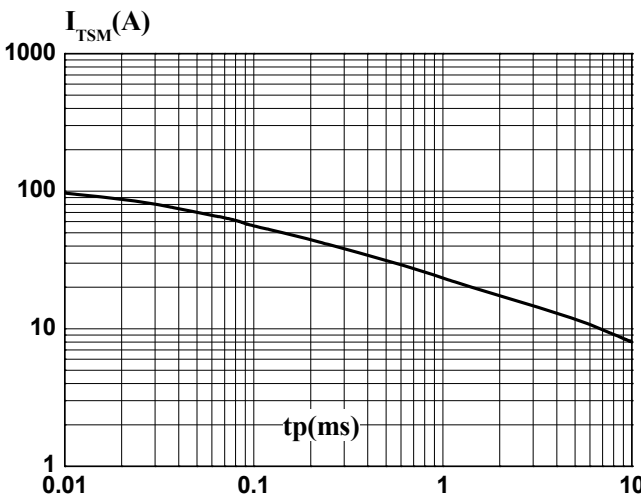
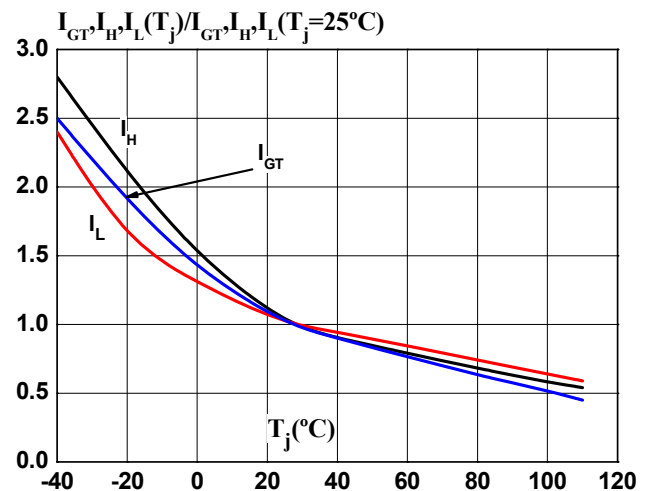


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Ordering information

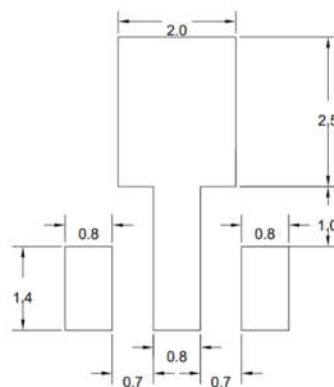
| Package | Packing Description | Base Quantity | Packing Quantity |
|---------|---------------------|---------------|-----------------------------|
| SOT-89 | Tape/Reel,7"reel | 1000pcs/Reel | 6000PCS/Box 30000PCS/Carton |

Package Dimensions

SOT-89

| Dim | Millimeter | | Inches | |
|-----|------------|------|--------|-------|
| | Min. | Max. | Min. | Max. |
| A | 1.40 | 1.60 | 0.055 | 0.063 |
| b | 0.32 | 0.52 | 0.013 | 0.020 |
| b1 | 0.38 | 0.58 | 0.015 | 0.023 |
| c | 0.35 | 0.45 | 0.014 | 0.018 |
| D | 4.40 | 4.60 | 0.173 | 0.181 |
| D1 | 1.45 | 1.65 | 0.057 | 0.065 |
| D2 | 1.70 | 1.80 | 0.067 | 0.071 |
| E | 2.30 | 2.60 | 0.091 | 0.102 |
| E1 | 3.95 | 4.25 | 0.156 | 0.167 |
| E2 | 1.80 | 2.00 | 0.071 | 0.079 |
| e | 1.40 | 1.60 | 0.055 | 0.063 |
| e1 | 2.80 | 3.20 | 0.110 | 0.126 |
| L | 0.90 | 1.20 | 0.035 | 0.047 |

The recommended mounting pad size



UNIT:MM

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